

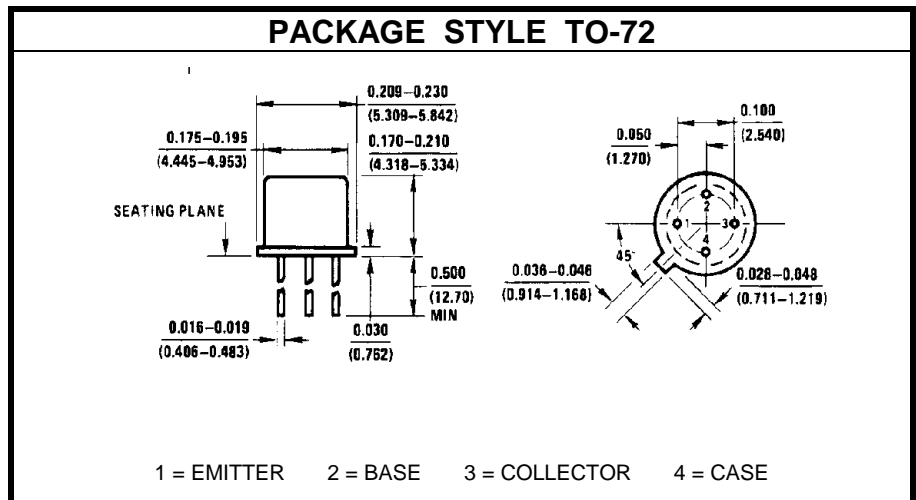
NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **ASI MM8006** is Designed for High Frequency Low Noise Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	50 mA
V_{CBO}	15 V
P_{DISS}	600 mW @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 3.0$ mA			10			V
BV_{CBO}	$I_C = 1.0$ μ A			15			V
I_{CBO}	$V_{CB} = 15$ V	$T_A = 150^\circ C$				0.01	μ A
	$V_{CB} = 15$ V					1.0	
BV_{EBO}	$I_E = 10$ μ A			3.0			V
h_{FE}	$V_{CE} = 1.0$ V	$I_C = 1.0$ mA		25			---
$V_{CE(SAT)}$	$I_C = 10$ mA	$I_B = 1.0$ mA				0.4	V
$V_{BE(SAT)}$	$I_C = 10$ mA	$I_B = 1.0$ mA				1.0	V
f_t	$V_{CE} = 10$ V	$I_C = 4.0$ mA	$f = 100$ MHz	1000			MHz
C_{ob}	$V_{CB} = 0$ V		$f = 140$ KHz			3.0	pF
	$V_{CB} = 10$ V		$f = 140$ KHz			1.7	
C_{ib}	$V_{EB} = 0.5$ V		$f = 140$ KHz			2.0	pF
N_F	$V_{CE} = 6.0$ V	$I_C = 1.0$ mA	$f = 60$ MHz			6.0	dB
G_{pe}	$V_{CB} = 12$ V	$I_C = 6.0$ mA	$f = 200$ MHz	15			dB
P_{out} η	$V_{CB} = 15$ V		$I_C = 8.0$ mA	30			mW
			$f = 500$ MHz	25			%